is provided with a means for impressing direct current or alternating current power.

Please add the following:

8. The semiconductor manufacturing apparatus according to Claim 2, wherein said vacuum vessel can be divided into a part including said processing chamber and a part having said substrate transport mechanism.

The semiconductor manufacturing apparatus according to 9. Claim 2 comprising a plasma generation mechanism for generating plasma in said processing chamber.

- The semiconductor manufacturing apparatus according to 10. Claim 3 comprising a plasma generation mechanism for generating plasma in said processing chamber.
- The semiconductor manufacturing apparatus according to Claim 10, wherein said plasma generation mechanism radiates microwave thorough a slot antenna.

## IN THE ABSTRACT

Please delete the abstract on file and replace it with the attached ABSTRACT OF THE DISCLOSURE.

Respectfully submitted,

Randall J. Knuth

Registration No. 34,644

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## RJK/jrc

Encs: ABSTRACT OF THE DISCLOSURE

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RANDALL J. KNUTH, P.C. 3510-A Stellhorn Road

Fort Wayne, IN 46815-4631 Telephone: 219/485-6001 Facsimile: 219/486-2794 Express Mail No. <u>EL161762383US</u>
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